Dual General Purpose Transistors

PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage BC856, SBC856 BC857, SBC857 BC858	V _{CEO}	-65 -45 -30	V
Collector – Base Voltage BC856, SBC856 BC857, SBC857 BC858	V _{CBO}	-80 -50 -30	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current –Continuous	I _C	-100	mAdc
Collector Current – Peak	Ic	-200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) T _A = 25°C Derate Above 25°C	P _D	380 250 3.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

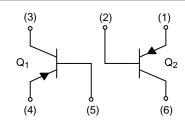


ON Semiconductor®

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SOT-363/SC-88 CASE 419B STYLE 1



MARKING DIAGRAM



3x = Specific Device Code x = B, F, G, or L

(See Ordering Information)

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

^{1.} $FR-5 = 1.0 \times 0.75 \times 0.062$ in

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = -10 mA) BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)CEO}	-65 -45 -30	- - -	- - -	V
Collector – Emitter Breakdown Voltage ($I_C = -10 \mu A$, $V_{EB} = 0$) BC856, SBC856 Series BC857B, SBC857B Only BC858 Series	V _{(BR)CES}	-80 -50 -30	- - -	- - -	V
Collector – Base Breakdown Voltage (I _C = -10 μA) BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)CBO}	-80 -50 -30	- - -	- - -	V
Emitter – Base Breakdown Voltage (I _E = -1.0 µA) BC856, SBC856 Series BC857, SBC857 Series BC858 Series	V _{(BR)EBO}	-5.0 -5.0 -5.0	- - -	- - -	V
Collector Cutoff Current $(V_{CB} = -30 \text{ V})$ $(V_{CB} = -30 \text{ V}, T_A = 150^{\circ}\text{C})$	I _{CBO}	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS			_		
DC Current Gain $ \begin{aligned} &(I_C = -10 \; \mu\text{A}, \; V_{CE} = -5.0 \; \text{V}) \\ & \; \; \text{BC856B}, \; \text{SBC856B}, \; \text{BC857B}, \; \text{SBC857B} \\ & \; \; \text{BC857C}, \; \text{SBC857C}, \; \text{BC858C} \\ &(I_C = -2.0 \; \text{mA}, \; V_{CE} = -5.0 \; \text{V}) \\ & \; \; \; \text{BC856B}, \; \text{SBC856B}, \; \text{BC857B}, \; \text{SBC857B} \\ & \; \; \text{BC857C}, \; \text{SBC857C}, \; \text{BC858C} \end{aligned} $	h _{FE}	- - 220 420	150 270 290 520	- - 475 800	-
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mA}$, $I_B = -0.5 \text{ mA}$) ($I_C = -100 \text{ mA}$, $I_B = -5.0 \text{ mA}$)	V _{CE(sat)}	_ _ _	_ _	-0.3 -0.65	V
Base – Emitter Saturation Voltage $(I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA})$ $(I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA})$	V _{BE(sat)}	<u>-</u>	-0.7 -0.9	_ _	V
Base – Emitter On Voltage ($I_C = -2.0 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$) ($I_C = -10 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$)	V _{BE(on)}	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					•
Current – Gain – Bandwidth Product $(I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	100	-	-	MHz
Output Capacitance $(V_{CB} = -10 \text{ V}, f = 1.0 \text{ MHz})$	C _{ob}	_	_	4.5	pF
Noise Figure (I _C = -0.2 mA, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	_	10	dB

TYPICAL CHARACTERISTICS - BC856/SBC856

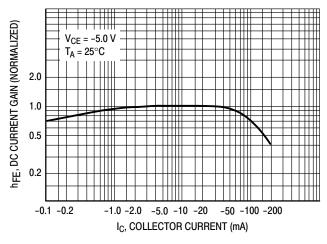


Figure 1. DC Current Gain

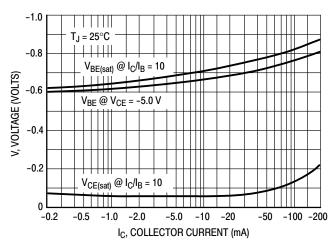


Figure 2. "On" Voltage

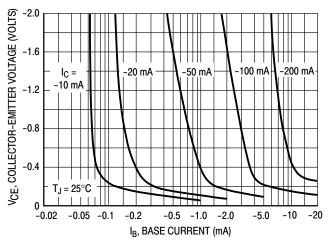


Figure 3. Collector Saturation Region

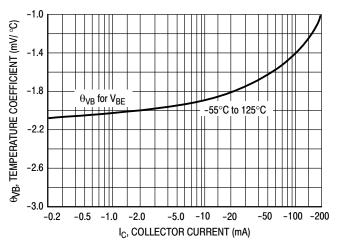


Figure 4. Base-Emitter Temperature Coefficient

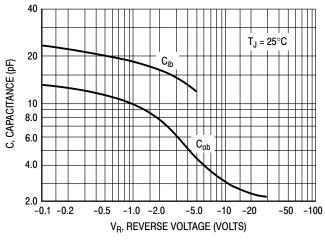


Figure 5. Capacitance

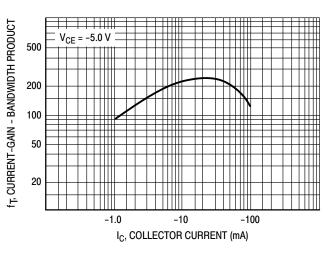
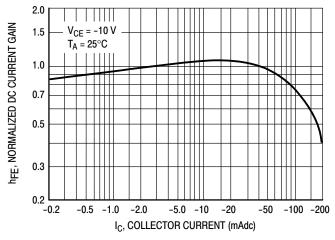


Figure 6. Current-Gain - Bandwidth Product

-1.0

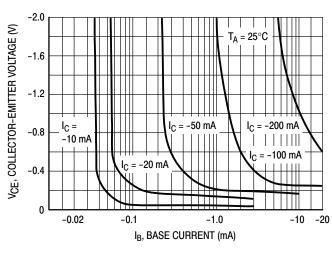
TYPICAL CHARACTERISTICS - BC857/SBC857/BC858



 $T_A = 25^{\circ}C$ -0.9 $V_{BE(sat)} @ I_C/I_B = 10$ -0.8 -0.7 V, VOLTAGE (VOLTS) $V_{BE(on)}$ @ $V_{CE} = -10 \text{ V}$ -0.6 -0.5 -0.4 -0.3 -0.2 $V_{CE(sat)} @ I_C/I_B = 10$ -0.1 -0.2 -0.1 -1.0 -2.0 -5.0 -50 -100 IC, COLLECTOR CURRENT (mAdc)

Figure 7. Normalized DC Current Gain

Figure 8. "Saturation" and "On" Voltages



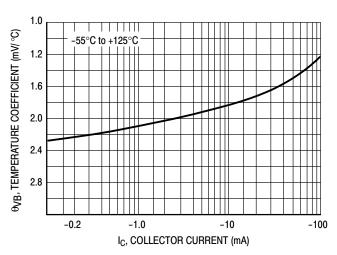
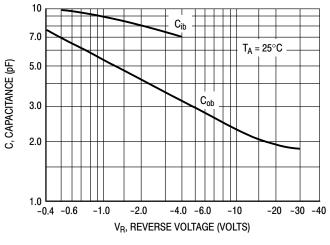


Figure 9. Collector Saturation Region

Figure 10. Base–Emitter Temperature Coefficient



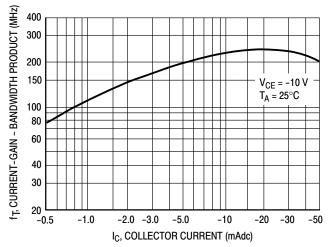


Figure 11. Capacitances

Figure 12. Current-Gain - Bandwidth Product

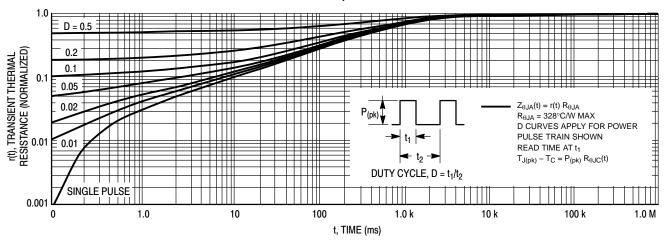


Figure 13. Thermal Response

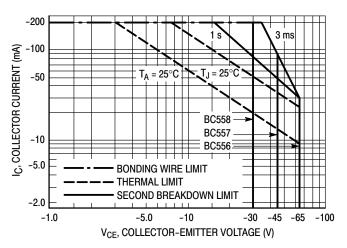


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

ORDERING INFORMATION

Device	Device Marking	Package	Shipping [†]
BC856BDW1T1G	3B	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC856BDW1T1G	3B	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC856BDW1T3G	3B	SOT-363 (Pb-Free)	10,000 / Tape & Reel
SBC856BDW1T3G	3B	SOT-363 (Pb-Free)	10,000 / Tape & Reel
BC857BDW1T1G	3F	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC857BDW1T1G	3F	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC857CDW1T1G	3G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC857CDW1T1G	3G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC858CDW1T1G	3L	SOT-363 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





E1

e

В

SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

DATE 18 APR 2024

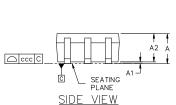
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

aaa

bbb

ccc ddd

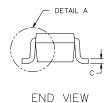


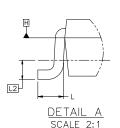
TOP VIEW

∆aaa H A−B

<u></u> БЬБ С

⊕ ddd M C A−B D





DIM	MIN.	NOM.	MAX.
А			1.10
A1	0.00		0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
С	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
е	0.65 BSC		
L	0.26	0.36	0.46
L2		0.15 BSC	

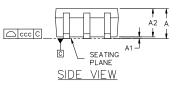
0.15

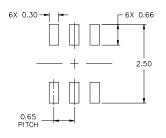
0.30

0.10

0.10

MILLIMETERS





RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

- *Date Code orientation and/or position may vary depending upon manufacturing location.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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